

**Product Summary**

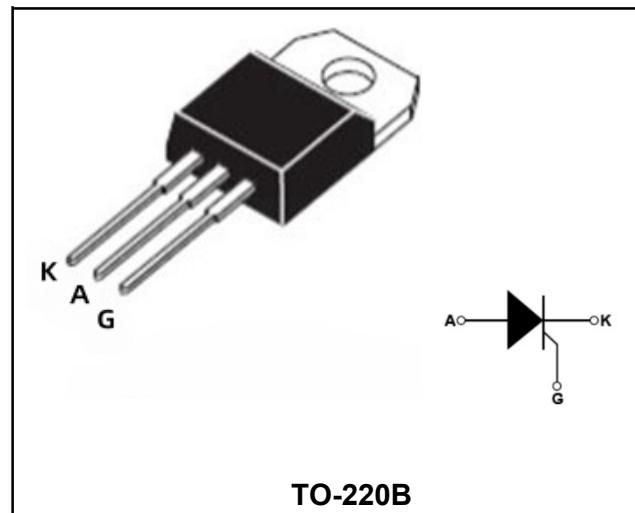
| Symbol                          | Value         | Unit |
|---------------------------------|---------------|------|
| $I_T(\text{RMS})$               | 40            | A    |
| $V_{\text{DRM}} V_{\text{RRM}}$ | 800/1000/1200 | V    |
| $V_{\text{TM}}$                 | 1.6           | V    |

**Features**

With high ability to withstand the shock loading of large current, Provide high dv/dt rate with strong resistance to electromagnetic interference.

**Application**

Power charger, T-tools, massager, solid state relay, AC Motor speed regulation and so on.



TO-220B

**Absolute maximum ratings (Ta=25°C unless otherwise noted)**

| Parameter  | Symbol            | Value         | Unit      |
|--|-------------------|---------------|-----------|
| Repetitive peak off-state voltage  | $V_{\text{DRM}}$  | 800/1000/1200 | V         |
| Repetitive peak reverse voltage  | $V_{\text{RRM}}$  | 800/1000/1200 | V         |
| RMS on-state current   | $I_T(\text{RMS})$ | 40            | A         |
| Non repetitive surge peak on-state current (full cycle, F=50Hz)                  | $I_{\text{TSM}}$  | 460           | A         |
| $I^2t$ value for fusing ( $t_p=10ms$ )   | $I^2t$            | 1060          | $A^2s$    |
| Critical rate of rise of on-state current ( $ I_G  = 2 \times  I_{G\text{T}} $ ) | $dI_T/dt$         | 100           | $A/\mu s$ |
| Peak gate current  | $I_{\text{GM}}$   | 4             | A         |
| Average gate power dissipation   | $P_G (\text{AV})$ | 1             | W         |
| Junction Temperature   | $T_J$             | -40~+125      | °C        |
| Storage Temperature  | $T_{\text{STG}}$  | -40 ~+150     | °C        |

## Electrical characteristics (TA=25°C, unless otherwise noted)

| Parameter                                    | Symbol              | Test Condition  | Value |     | Unit |
|--|---------------------|---|-------|-----|------|
|  |                     |   | Min   | Max |      |
| Gate trigger current                         | I <sub>GT</sub>     | V <sub>D</sub> =12V, R <sub>L</sub> =33Ω, T <sub>j</sub> =25°C                  | 5     | 35  | mA   |
| Gate trigger voltage                         | V <sub>GT</sub>     |   | -     | 1.3 | V    |
| Gate non-trigger voltage                     | V <sub>GD</sub>     | V <sub>D</sub> =V <sub>DRM</sub> , R <sub>L</sub> =3.3kΩ, T <sub>j</sub> =125°C | 0.2   | -   | V    |
| latching current                             | I <sub>L</sub>      | I <sub>G</sub> = 1.2I <sub>GT</sub>   | -     | 150 | mA   |
| Holding current                              | I <sub>H</sub>      | I <sub>T</sub> =500mA   | -     | 75  | mA   |
| Critical-rate of rise of commutation voltage | dV <sub>D</sub> /dt | V <sub>D</sub> =67%V <sub>DRM</sub> , Gate Open T <sub>j</sub> =125°C           | 500   | -   | V/μs |

## STATIC CHARACTERISTICS

|                                   |                  |   |                       |     |    |    |
|-----------------------------------|------------------|---|-----------------------|-----|----|----|
| Forward "on" voltage              | V <sub>TM</sub>  | I <sub>T</sub> =80A, t <sub>p</sub> =380μs, T <sub>j</sub> =25°C  | -                     | 1.6 | V  |    |
| Repetitive Peak Off-State Current | I <sub>DRM</sub> | V <sub>D</sub> =V <sub>DRM</sub> V <sub>R</sub> =V <sub>RRM</sub> | T <sub>j</sub> =25°C  | -   | 10 | μA |
| Repetitive Peak Reverse Current   | I <sub>RRM</sub> |   | T <sub>j</sub> =125°C | -   | 4  | mA |

## THERMAL RESISTANCES

|                    |                      |                     |      |     |      |
|--------------------|----------------------|---------------------|------|-----|------|
| Thermal resistance | R <sub>th(j-c)</sub> | Junction to case    | TYP. | 0.8 | °C/W |
|                    | R <sub>th(j-a)</sub> | Junction to ambient | TYP. | 60  | °C/W |

## Ordering Information

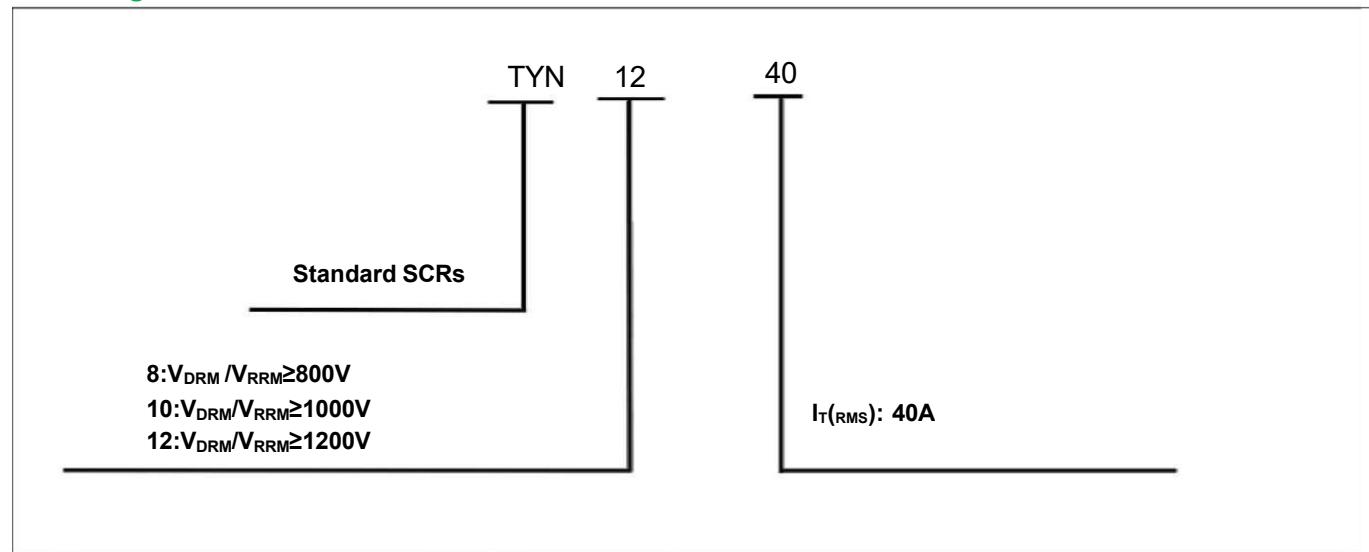


FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

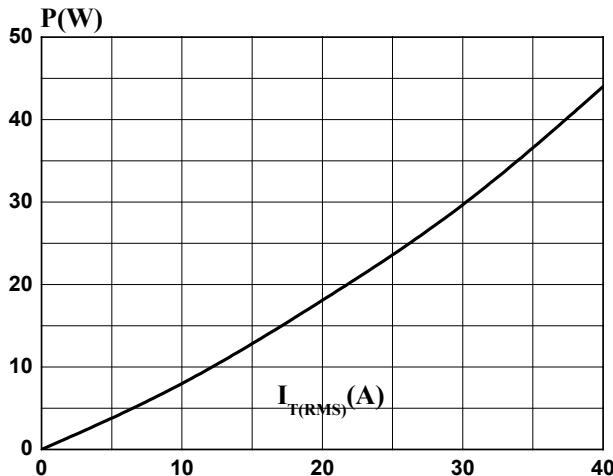


FIG.2: RMS on-state current versus case temperature (full cycle)

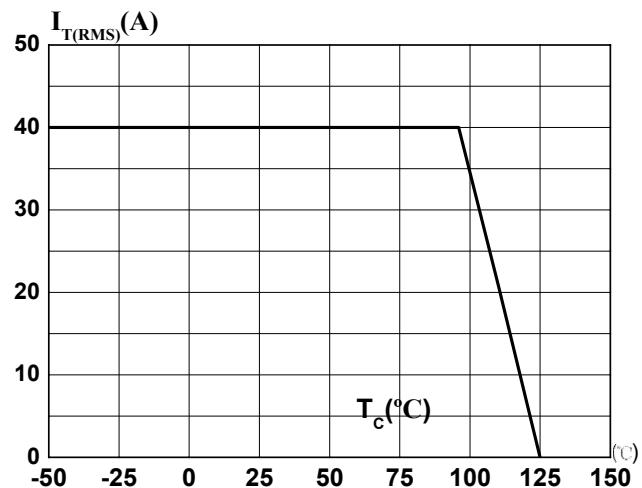


FIG.3: Surge peak on-state current versus number of cycles

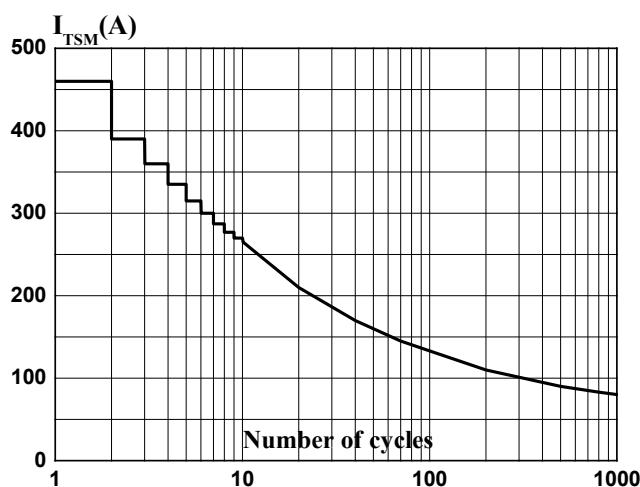


FIG.4: On-state characteristics (maximum values)

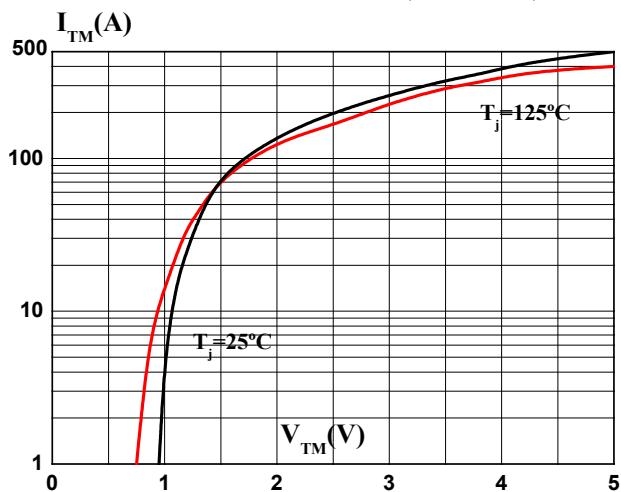


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$

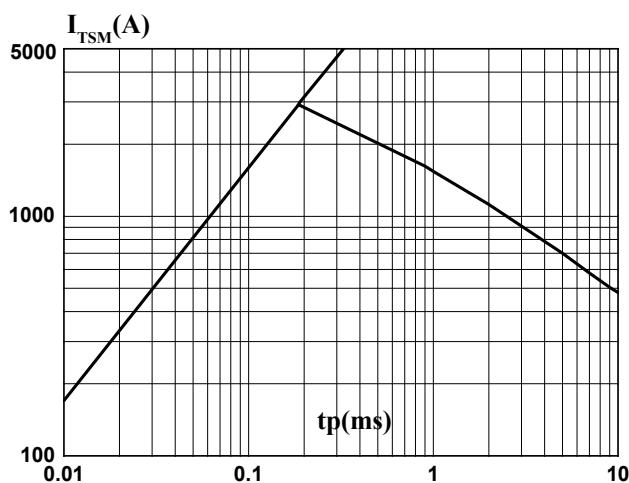
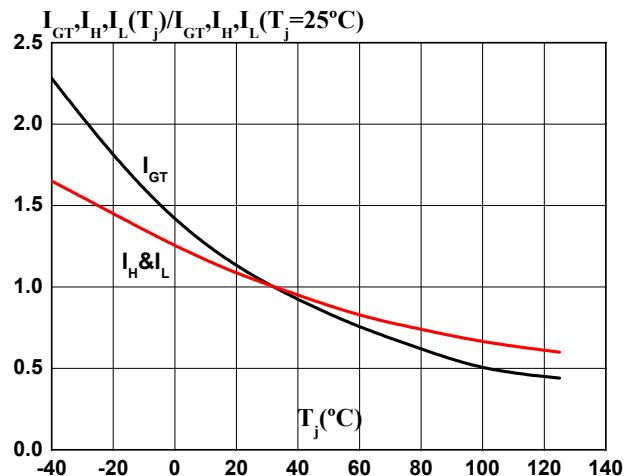
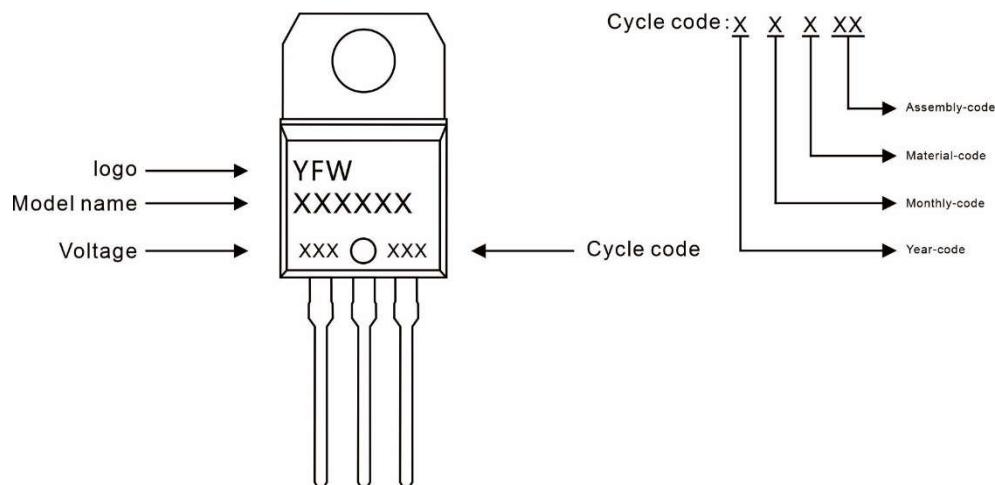


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



### Marking Diagram



### Ordering information

| Model name | Package | Unit Weight   | Base Quantity | Packing Quantity           |
|------------|---------|---------------|---------------|----------------------------|
| TYNXXXX    | TO-220B | 0.07oz(1.96g) | 50pcs/tube    | 1000PCS/Box 5000PCS/Carton |

### Package Dimensions

TO-220B(Non Insulated)

| Symbol | Millimeter |       | Inches |       |
|--------|------------|-------|--------|-------|
|        | Min.       | Max.  | Min.   | Max.  |
| A      | 9.80       | 10.40 | 0.386  | 0.409 |
| B      | 2.65       | 3.10  | 0.104  | 0.122 |
| C      | 14.80      | 16.10 | 0.583  | 0.634 |
| D      | 0.70       | 0.92  | 0.028  | 0.036 |
| D1     | 1.18       | 1.42  | 0.047  | 0.056 |
| E      | 2.40       | 2.70  | 0.095  | 0.106 |
| L      | 2.80       | 4.20  | 0.11   | 0.17  |
| L1     | 13.05      | 13.60 | 0.514  | 0.535 |
| H      | 5.85       | 6.82  | 0.23   | 0.27  |
| K      | 2.35       | 2.75  | 0.093  | 0.108 |
| T      | 4.38       | 4.61  | 0.172  | 0.181 |
| T1     | 1.15       | 1.36  | 0.045  | 0.054 |
| T2     | 0.35       | 0.65  | 0.014  | 0.026 |
| ΦR     | 3.75       | 3.95  | 0.148  | 0.156 |

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